SWD7802

30V Dual N-Channel Enhancement-Mode MOSFET

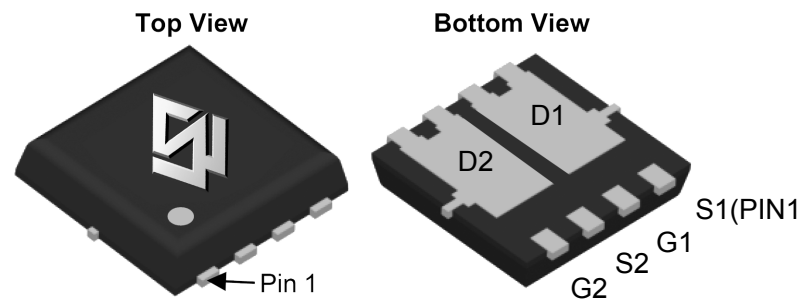
General Description

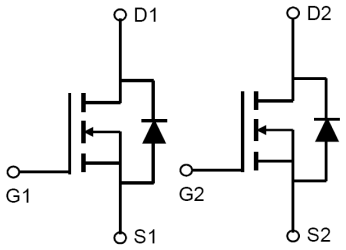
- Low resistance.
- Use as a load switch.
- Use in PWM applications

Product Summary

- BV_{DSS} 30V
- $R_{DS(on)}$ @VGS = 10V < 14mΩ
- $R_{DS(on)}$ @VGS = 4.5V < 18mΩ

PDFN3X3-8L





Absolute Maximum Ratings (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current (T_A=25ºC)	I_D	8	A
Drain Current (T_A=75ºC)		4.5	A
Pulsed Drain Current [a]	I_{DM}	40	A
Avalanche Energy (L= 0.1 mH)	E_{AS}	25	mJ
Power Dissipation [b] (T_A=25ºC)	P_D	2	W
Power Dissipation [b] (T_A=75ºC)		1.2	W
Junction and Storage Temperature Range	T_J, T_{STG}	-55 ~ +150	ºC

Thermal Characteristics

Parameter	Symbol	Maximum	Units
Junction-to-Ambient [a] (t ≤ 10s)	$R_{\theta JA}$	42	ºC/W
Junction-to-Ambient [a,d] (Steady-State)		62	ºC/W
Junction-to-Lead (Steady-State)	$R_{\theta JL}$	4	ºC/W

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Electrical Characteristics (T_A = 25°C unless otherwise noted)						
Symbol	**Parameter**	**Conditions**	**Min**	**Typ**	**Max**	**Units**
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V , I_D = 250uA	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 30V , V_{GS} = 0V			1	uA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V			±100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS} , I_D = 250uA	1.0	1.8	2.5	V
$R_{DS(ON))}$	Drain-Source On-State Resistance	V_{GS} = 10V , I_D = 10A		10	14	mΩ
		V_{GS} = 4.5V , I_D = 6A		15	18	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 5.0V , I_D = 12A		35		S
Drain-Source Diode Characteristics						
V_{SD}	Diode Forward Voltage	V_{GS} = 0V , I_S = 1.0A			1.1	V
I_S	Maximum Body-Diode Continuous Current				40	A
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 15V , V_{GS} = 0V f = 1.0MHz		940		pF
C_{oss}	Output Capacitance			132		pF
C_{rss}	Reverse Transfer Capacitance			111		pF
Switching Characteristics						
Q_g	Total Gate Charge	V_{DS} = 15V , I_D = 15A V_{GS} = 4.5V		10.2		nC
Q_{gs}	Gate-Source Charge			4.3		nC
Q_{gd}	Gate-Drain Charge			3.5		nC
$t_{D(ON)}$	Turn-On Delay Time	V_{DD} = 15V , ID = 15A V_{GS} = 10 V R_{GEN} = 3.3 ohm		5		ns
t_r	Turn-On Rise Time			8		ns
$t_{D(OFF)}$	Turn-Off Delay Time			32		ns
t_f	Turn-Off Fall Time			4		ns

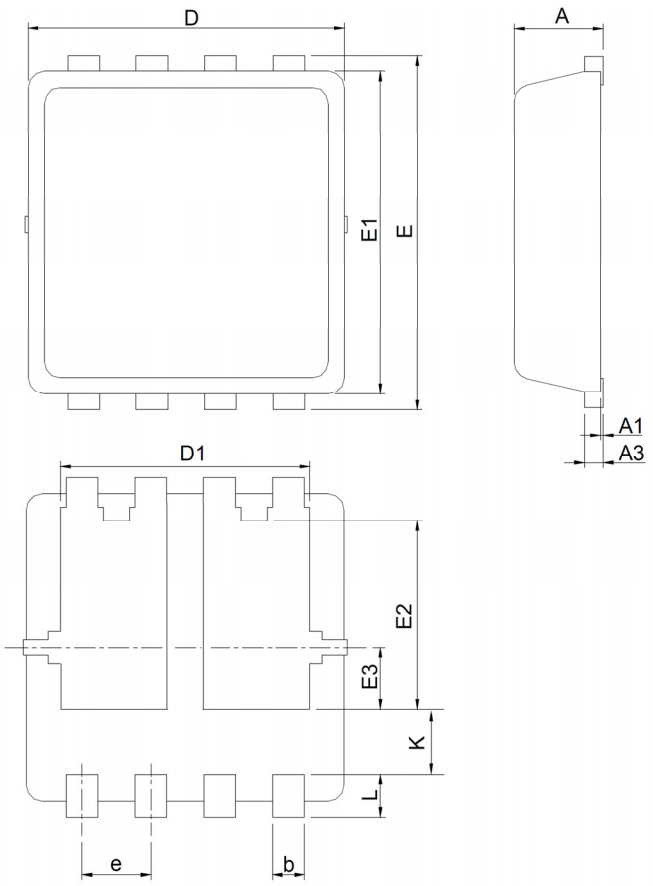
a. Repetitive rating, Pulse width limited by junction temperature $T_{J(MAX)}$=150 ºC. Ratings are based on low frequency and duty cycles to keep initial T_J=25 ºC

b. The power dissipation P_D is based on $T_{J(MAX)}$=150 ºC , using≤10s junction-to-ambient thermal resistance.

c. The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A = 25°C. The value in any given application depends on the user's specific board design.

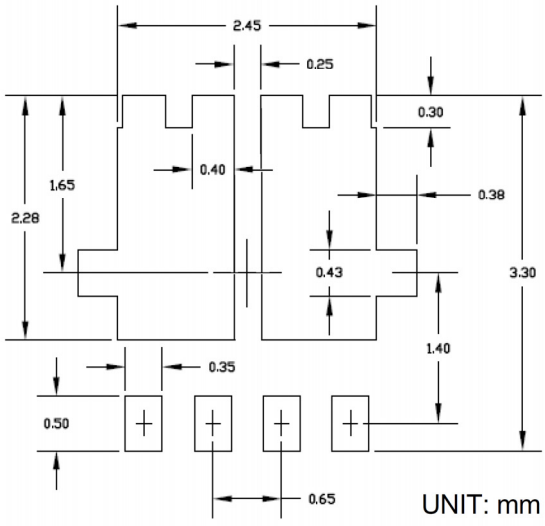
d. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

PDFN3x3-8L Package



SYMBOL	DFN3x3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.80	1.00	0.031	0.039
A1	0.00	0.05	0.000	0.002
A3	0.10	0.25	0.004	0.010
b	0.24	0.35	0.009	0.014
D	2.90	3.10	0.114	0.122
D1	2.25	2.45	0.089	0.096
E	3.10	3.30	0.122	0.130
E1	2.90	3.10	0.114	0.122
E2	1.65	1.85	0.065	0.073
E3	0.56	0.58	0.022	0.023
e	0.65 BSC		0.026 BSC	
K	0.475	0.775	0.019	0.031
L	0.30	0.50	0.012	0.020

RECOMMENDED LAND PATTERN



单击下面可查看定价，库存，交付和生命周期等信息

>>SiliconWisdom(矽睿半导体)